

10-518945  
DT05 Rec'd PCT/PTO 09 DEC 2004  
PTO/SB/08A (04-03)

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Sheet	1	of	2
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<b>Application Number</b>	
<b>Filing Date</b>	
<b>First Named Inventor</b>	<b>Yoshihiro ITO</b>
<b>Art Unit</b>	
<b>Examiner Name</b>	
<b>Attorney Docket Number</b>	<b>36856.1310</b>

[illegible]

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM -YYYY	Country of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>2</sup> Number-Kind Code <sup>5</sup> (if known)				
/TN/	1	JP 2002-326895 (English abstract and machine translation)	11/2002	JAPAN		x
/TN/	2	JP 2001-244464 (English abstract and machine translation)	09/2001	JAPAN		x
/TN/	3	JP 2000-150900 (English abstract and machine translation)	05/2000	JAPAN		x
/TN/	4	JP 2002-319682 (English abstract and machine translation)	10/2002	JAPAN		x
/TN/	5	JP 10-306372 (English abstract and machine translation)	11/1998	JAPAN		x
/TN/	6	EP 1 134 811	09/2001	EPO	1	x
/TN/	7	JP 05-171435 (English abstract and machine translation)	07/1993	JAPAN		x
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /TN/

/Thanh Nguyen/

09/24/2008

Receipt date: 12/09/2004

10618845 CA 12893

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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

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Sheet 2 of 2

Application Number	
Filing Date	
First Named Inventor	Yoshihiro ITO
Art Unit	
Examiner Name	
Attorney Docket Number	36856.1310

## **NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title Of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
/TN/	9	Yutaka OHYA et al., "THIN FILM TRANSISTOR OF ZnO FABRICATED BY CHEMICAL SOLUTION DEPOSITION", Jpn. J. Appl. Phys., Vol. 40 (2001), pp. 297- 298, Part 1, No. 1, January 2001.	
/TN/	10	K. YAMAYA et al., "USE OF HELICON-WAVE EXCITED PLASMA FOR ALUMINUM- DOPED ZnO THIN-FILM SPUTTERING", Appl. Phys. Lett. 72 (2), January 12, 1998, pp. 235-237.	
/TN/	11	S.K. HONG et al., "ZnO AND RELATED MATERIALS: PLASMA-ASSISTED MOLECULAR BEAM EPITAXIAL GROWTH, CHARACTERIZATION, AND APPLICATION", Journal of Electronic Materials, Vo. 30, No. 6, 2001, pp. 647-658.	
/TN/	12	Shen ZHU et al., "POLARITY EFFECTS OF SUBSTRATE SURFACE IN HOMOEPITAXIAL ZnO FILM GROWTH", Journal of Crystal Growth 219 (2000), pp. 361-367.	
/TN/	13	Yefan CHEN et al., "MORPHOLOGY EVOLUTION OF ZnO (000 1) SURFACE DURING PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY", Applied Physics Letters, Volume 80, Number 8, 02/2002, pp. 1358-1360.	
/TN/	14	Soon-Ku HONG et al., "CONTROL OF POLARITY OF ZnO FILMS GROWN BY PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY: Zn- AND O-POLAR ZnO FILMS ON Ga-POLAR AND GaN TEMPLATES", Applied Physics Letters, Volume 77, Number 22, 11/2000, pp. 3571-3573.	

Examiner Signature	/Thanh Nguyen/	Date Considered	09/24/2008
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